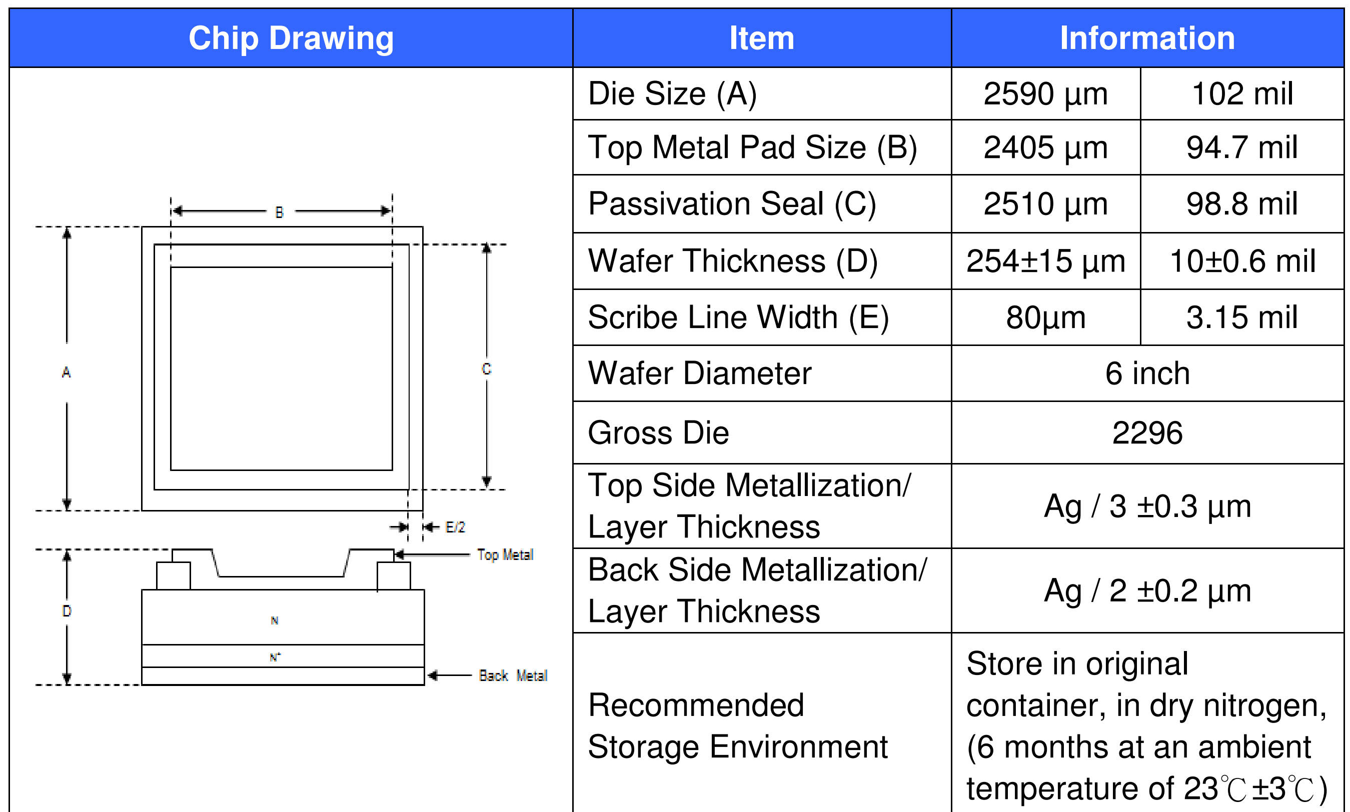
BM2150BG

150V, 20A(1), XTBR series Schottky

Mechanical Data



Chip Drawing	Item	Information	
	Die Size (A)	2590 µm	102 mil
	Top Metal Pad Size (B)	2405 µm	94.7 mil
	Passivation Seal (C)	2510 µm	98.8 mil
	Wafer Thickness (D)	254±15 µm	10±0.6 mil
	Scribe Line Width (E)	80µm	3.15 mil
	Wafer Diameter	6 inch	
	Gross Die	2296	
	Top Side Metallization/ Layer Thickness	Ag / 3 ±0.3 µm	
	Back Side Metallization/ Layer Thickness	Ag / 2 ±0.2 µm	
	Recommended Storage Environment	Store in original container, in dry nitrogen, (6 months at an ambient temperature of 23℃±3℃)	

Electrical Characteristics in C/P test（T_J=25℃）

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V_{BR}	Reverse Breakdown Voltage	150	—	—	V	I_R =300µA
V_F	Instantaneous Forward Voltage	—	0.60	0.65	V	I_F =3A(2)
		—	0.78	0.84	V	I_F =10A(2)
I_R	Reverse Leakage Current	—	8	15	µA	V_R =150V
T_J, T_{STG}	Operating and Storage Temperature	-40℃ to 150℃ Max				